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MEMC 98-1451/2554.1
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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Application of Robert J. Falster, et al

Serial No. 10/073,506

Filed February 11, 2002

Confirmation No. 6190

For ANNEALING PROCESS FOR PRODUCING LOW DEFECT DENSITY SILICON
(AS AMENDED)

May 16, 2002

TO THE COMMISSIONER OF PATENTS AND TRADEMARKS,

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INFORMATION DISCLOSURE STATEMENT

In accordance with 37 C.F.R. 1.97 and 1.98 and MPEP 609, and in compliance with the duty of disclosure set forth in 37 C.F.R. 1.56, applicants submit copies of the references listed on the attached PTO/SB/08A for consideration by the Patent and Trademark Office in the above-entitled application and to be made of record therein.

This application is a divisional of U.S. Application Serial No. 09/416,998, filed October 13, 1999. Pursuant to M.P.E.P. §609, Applicants are not submitting copies of Reference Nos. 1-40, 42, 45-61, 64-68, 70-91, 93-110, 112-126, 128-136 and 139-140, which were previously made of record in application Serial No. 09/385,108. Applicants are enclosing herewith copies of Reference Nos. 41, 43-44, 62-63, 69, 92, 111, 127 and 137-138.

Please note that there were several translations previously submitted with Application Serial No. 09/416,998, as well as new translations submitted herewith, and Applicants make no representation as to accuracy or completeness of those translations.

The Commissioner is hereby authorized to charge any fees incurred regarding this Information Disclosure Statement to Account No. 19-1345 if an Office Action was issued prior to the date of mailing of this Statement.

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Respectfully submitted,



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